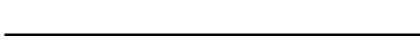
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April 1st, 2010 Renesas Electronics Corporation

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MOS FIELD EFFECT TRANSISTOR μ PA2754GR

SWITCHING N-CHANNEL POWER MOS FET

DESCRIPTION

The μ PA2754GR is Dual N-channel MOS Field Effect Transistor designed for Li-ion battery protection circuit and power management application.

FEATURES

- · Dual chip type
- Low on-state resistance

RDS(on)1 = 14.5 m Ω MAX. (Vgs = 4.5 V, ID = 5.5 A)

 $R_{\text{DS(on)2}}$ = 15.0 $m\Omega$ MAX. (Vgs = 4.0 V, Ip = 5.5 A)

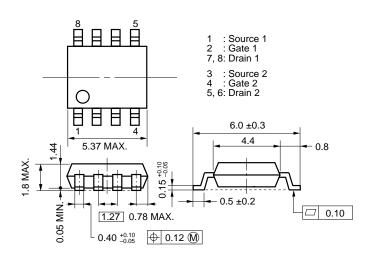
RDS(on)4 = 18.6 m Ω MAX. (Vgs = 2.5 V, ID = 5.5 A)

- Low Ciss: Ciss = 1940 pF TYP. (VDS = 10 V, VGS = 0 V)
- Built-in G-S protection diode
- Small and surface mount package (Power SOP8)

ORDERING INFORMATION

PART NUMBER	PACKAGE
μPA2754GR	Power SOP8

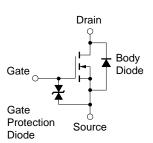
PACKAGE DRAWING (Unit: mm)



ABSOLUTE MAXIMUM RATINGS (TA = 25°C, All terminals are connected.)

Drain to Source Voltage (Vgs = 0 V)	VDSS	30	V
Gate to Source Voltage (Vps = 0 V)	Vgss	±12	V
Drain Current (DC) Note2	ID(DC)	±11	Α
Drain Current (pulse) Note1	D(pulse)	±88	Α
Total Power Dissipation (2 units) Note2	P⊤	2.0	W
Total Power Dissipation (1 unit) Note2	PT	1.7	W
Channel Temperature	Tch	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C
Single Avalanche Current Note3	las	11	Α
Single Avalanche Energy Note3	Eas	12.1	mJ

EQUIVALENT CIRCUIT (1/2 circuit)



- **Notes 1.** PW \leq 10 μ s, Duty cycle \leq 1%
 - 2. $T_A = 25$ °C, Mounted on ceramic substrate of 2000 mm² x 2.2 mm
 - 3. Starting Tch = 25°C, Vdd = 15 V, Rg = 25 Ω , Vgs = 12 \rightarrow 0 V

Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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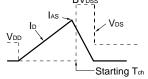
ELECTRICAL CHARACTERISTICS (TA = 25°C, All terminals are connected.)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	Vps = 30 V, Vgs = 0 V			1	μΑ
Gate Leakage Current	Igss	Vgs = ±12 V, Vps = 0 V			±10	μΑ
Gate Cut-off Voltage Note	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	0.5		1.5	V
Forward Transfer Admittance Note	y _{fs}	V _{DS} = 10 V, I _D = 5.5 A	8	16		S
Drain to Source On-state Resistance Note	RDS(on)1	Vgs = 4.5 V, ID = 5.5 A		11.5	14.5	mΩ
	R _{DS(on)2}	Vgs = 4.0 V, ID = 5.5 A		11.8	15.0	mΩ
	R _{DS(on)3}	Vgs = 3.1 V, ID = 5.5 A		12.7	16.9	mΩ
	R _{DS(on)4}	Vgs = 2.5 V, ID = 5.5 A		13.9	18.6	mΩ
Input Capacitance	Ciss	V _{DS} = 10 V		1940		pF
Output Capacitance	Coss	Vgs = 0 V		385		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		270		pF
Turn-on Delay Time	td(on)	VDD = 15 V, ID = 5.5 A		21		ns
Rise Time	tr	Vgs = 4.5 V		45		ns
Turn-off Delay Time	td(off)	$R_G = 10 \Omega$		75		ns
Fall Time	t f			30		ns
Total Gate Charge	Q _G	VDD = 24 V		25		nC
Gate to Source Charge	Qgs	Vgs = 4.5 V		3		nC
Gate to Drain Charge	Q _{GD}	ID = 11 A		10		nC
Body Diode Forward Voltage	V _{F(S-D)}	If = 11 A, Vgs = 0 V		0.81	1.2	V
Reverse Recovery Time	trr	IF = 11 A, VGS = 0 V		47		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/μs		41		nC

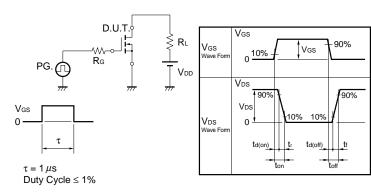
Note Pulsed: PW \leq 350 μ s, Duty Cycle \leq 2%

TEST CIRCUIT 1 AVALANCHE CAPABILITY

$V_{GS} = 20 \rightarrow 0 \text{ V}$ $PG. \bigcirc PG. \bigcirc PG.$

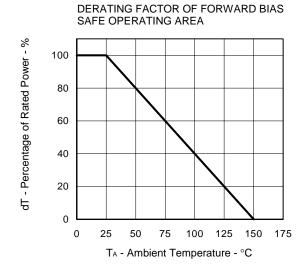


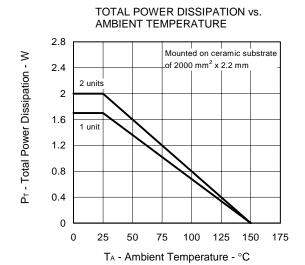
TEST CIRCUIT 2 SWITCHING TIME



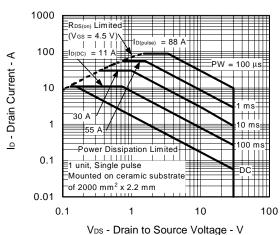
TEST CIRCUIT 3 GATE CHARGE

TYPICAL CHARACTERISTICS (TA = 25°C, All terminals are connected.)

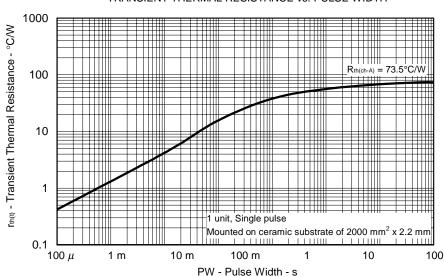




FORWARD BIAS SAFE OPERATING AREA



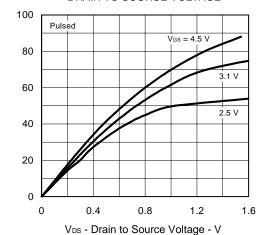
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



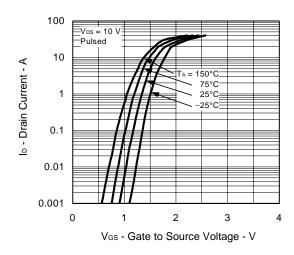
Data Sheet G15816EJ1V0DS 3

Ip - Drain Current - A

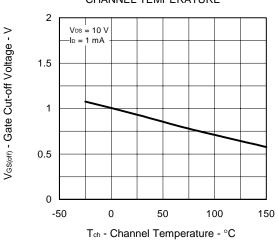
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



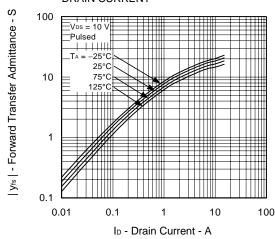
FORWARD TRANSFER CHARACTERISTICS



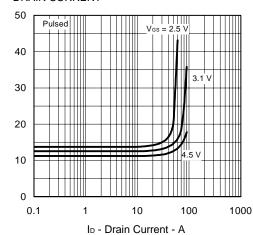
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



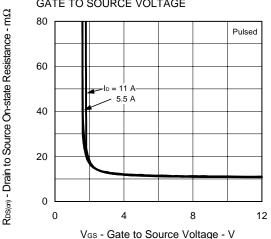
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

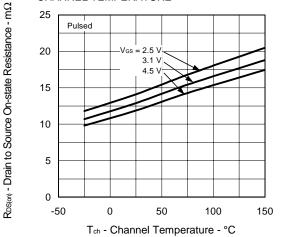


DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

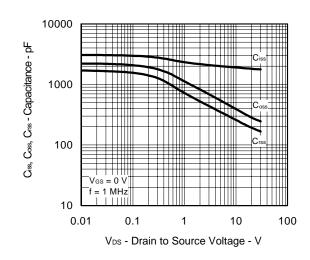


R_{DS(σ1)} - Drain to Source On-state Resistance - mΩ

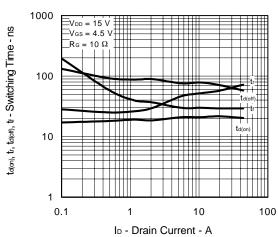
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



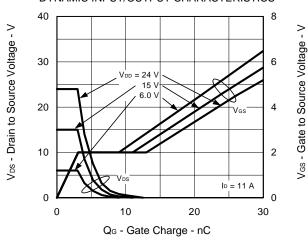
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



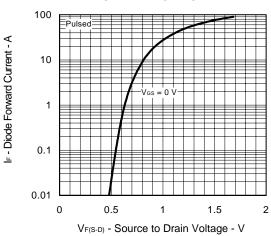
SWITCHING CHARACTERISTICS



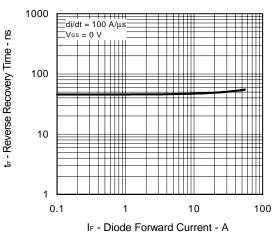
DYNAMIC INPUT/OUTPUT CHARACTERISTICS

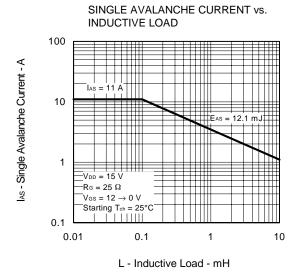


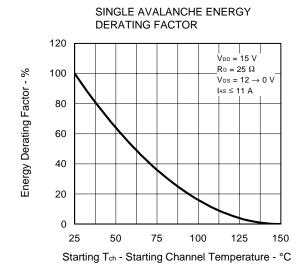
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT







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